DATA SHEET

For a complete data sheet, please also download:

- The IC06 74HC/HCT/HCU/HCMOS Logic Family Specifications
- The IC06 74HC/HCT/HCU/HCMOS Logic Package Information
- The IC06 74HC/HCT/HCU/HCMOS Logic Package Outlines

74HC4050
Hex high-to-low level shifter

Product specification
File under Integrated Circuits, IC06

December 1990

Philips Semiconductors

PHILIPS

Hex high-to-low level shifter 74HC4050

FEATURES

- Output capability: standard
- I_{CC} category: SSI

GENERAL DESCRIPTION

The 74HC4050 is a high-speed Si-gate CMOS device and is pin compatible with the “4050” of the “4000B” series. It is specified in compliance with JEDEC standard no. 7A.

The 74HC4050 provides six non-inverting buffers with a modified input protection structure, which has no diode connected to V_{CC}. Input voltages of up to 15 V may therefore be used. This feature enables the non-inverting buffers to be used as logic level translators, which will convert high level logic to low level logic, while operating from a low voltage power supply. For example 15 V logic (“4000B series”) can be converted down to 2 V logic.

The actual input switch level remains related to the V_{CC} and is the same as mentioned in the family characteristics.

APPLICATIONS

- Converting 15 V logic (“4000B” series) down to 2 V logic.

QUICK REFERENCE DATA

GND = 0 V; T_{amb} = 25 °C; $t_r = t_f$ = 6 ns

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
			HC	
t_{PHL} / t_{PLH}	propagation delay nA to nY	C_L = 15 pF; V_{CC} = 5 V	7	ns
C_I	input capacitance		3.5	pF
C_{PD}	power dissipation capacitance per buffer	note 1	14	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

   $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

   f_i = input frequency in MHz

   f_o = output frequency in MHz

   C_L = output load capacitance in pF

   V_{CC} = supply voltage in V

   $\sum (C_L \times V_{CC}^2 \times f_o)$ = sum of outputs

ORDERING INFORMATION

See *“74HC/HCT/HCU/HCMOS Logic Package Information”*.

PIN DESCRIPTION

PIN NO.	SYMBOL	NAME AND FUNCTION
1	V_{CC}	positive supply voltage
2, 4, 6, 10, 12, 15	1Y to 6Y	data outputs
3, 5, 7, 9, 11, 14	1A to 6A	data inputs
8	GND	ground (0 V)
13, 16	n.c.	not connected

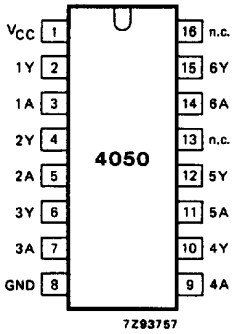


Fig.1 Pin configuration.

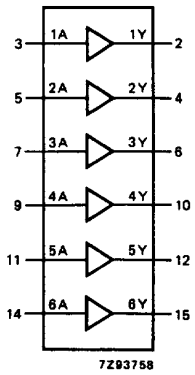


Fig.2 Logic symbol.

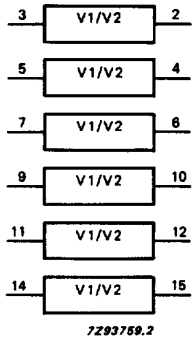


Fig.3 IEC logic symbol.

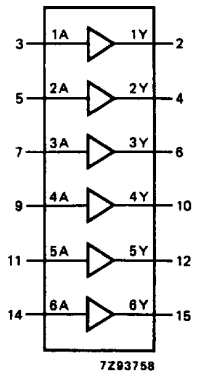


Fig.4 Functional diagram.

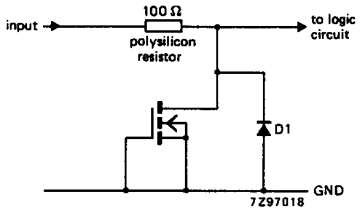


Fig.5 Input protection for HC4050. Single sided thick oxide field effect metal gate transistor as input protection.

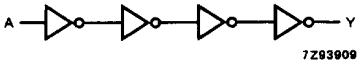


Fig.6 Logic diagram (one level shifter).

FUNCTION TABLE (1)

INPUT	OUTPUT
nA	**nY**
L H	L H

Note

1. H = HIGH voltage level
   L = LOW voltage level

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)
Voltages are referenced to GND (ground = 0 V)

SYMBOL	PARAMETER	MIN.	MAX.	UNIT	CONDITIONS
V_{CC}	DC supply voltage	–0.5	+7	V	
V_{IK}	DC input voltage range	–0.5	+16	V	
$-I_{IK}$	DC input diode current		20	mA	for $V_I < -0.5$ V
$\pm I_{OK}$	DC output diode current		20	mA	for $V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V
$\pm I_O$	DC output source or sink current - standard outputs		25	mA	for -0.5 V $< V_O < V_{CC} + 0.5$ V
$\pm I_{CC}$; $\pm I_{GND}$	DC V_{CC} or GND current for types with: - standard outputs		50	mA	
T_{stg}	storage temperature range	–65	+150	°C	
P_{tot}	power dissipation per package plastic DIL		750	mW	for temperature range: –40 to +125 °C 74HC above +70 °C: derate linearly with 12 mW/K
	plastic mini-pack (SO)		500	mW	above +70 °C: derate linearly with 8 mW/K

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	74HC			UNIT	CONDITIONS
		min.	typ.	max.		
V_{CC}	DC supply voltage	2.0	5.0	6.0	V	
V_I	DC input voltage range	GND	–	15	V	
T_{amb}	operating ambient temperature range	–40		+85	°C	see DC and AC characteristics
T_{amb}	operating ambient temperature range	–40		+125	°C	
t_r, t_f	input rise and fall times		6.0	1000 500 400 650 1000	ns	V_{CC} = 2.0 V; V_{IN} = 2.0 V V_{CC} = 4.5 V; V_{IN} = 4.5 V V_{CC} = 6.0 V; V_{IN} = 6.0 V V_{CC} = 6.0 V; V_{IN} = 10.0 V V_{CC} = 6.0 V; V_{IN} = 15.0 V

DC CHARACTERISTICS FOR 74HC

Voltages are referenced to GND (ground = 0 V)

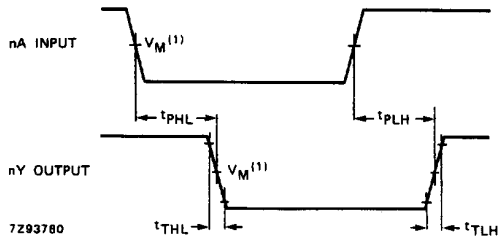
SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS		
		74HC								V_{CC} (V)	V_I	OTHER
		+25			−40 to +85		−40 to +125					
		min.	typ.	max.	min.	max.	min.	max.				
V_{IH}	HIGH level input voltage	1.5 3.15 4.2	1.3 2.4 3.1		1.5 3.15 4.2		1.5 3.15 4.2		V	2.0 4.5 6.0		
V_{IL}	LOW level input voltage		0.7 1.8 2.3	0.5 1.35 1.8		0.5 1.35 1.8		0.5 1.35 1.8	V	2.0 4.5 6.0		
V_{OH}	HIGH level output voltage - all outputs	1.9 4.4 5.9	2.0 4.5 6.0		1.9 4.4 5.9		1.9 4.4 5.9		V	2.0 4.5 6.0	V_{IH} or V_{IL}	$-I_O$ = 20 μA $-I_O$ = 20 μA $-I_O$ = 20 μA
V_{OH}	HIGH level output voltage - standard outputs	3.98 5.48			3.84 5.34		3.7 5.2		V	4.5 6.0	V_{IH} or V_{IL}	$-I_O$ = 4.0 mA $-I_O$ = 5.2 mA
V_{OL}	LOW level output voltage - all outputs			0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V	2.0 4.5 6.0	V_{IH} or V_{IL}	I_O = 20 μA I_O = 20 μA I_O = 20 μA
V_{OL}	LOW level output voltage - standard outputs			0.26 0.26		0.33 0.33		0.4 0.4	V	4.5 6.0	V_{IH} or V_{IL}	I_O = 4.0 mA I_O = 5.2 mA
± I_I	input leakage current			0.1		1.0		1.0	μA	6.0	V_{CC} or GND	
				0.5		5.0		5.0	μA	2.0 to 6.0	15 V	
I_{CC}	quiescent supply current			2.0		20.0		40.0	μA	6.0	15 V or GND	

AC CHARACTERISTICS FOR 74HC

GND = 0 V; $t_r = t_f$ = 6 ns; C_L = 50 pF

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS	
		74HC								V_{CC} (V)	WAVEFORMS
		+25			–40 to +85		–40 to +125				
		min.	typ.	max.	min.	max.	min.	max.			
t_{PHL}/ t_{PLH}	propagation delay nA to nY		25 9 7	85 17 14		105 21 18		130 26 22	ns	2.0 4.5 6.0	Fig.7
t_{THL}/ t_{TLH}	output transition time		19 7 6	75 15 13		95 19 16		110 22 19	ns	2.0 4.5 6.0	Fig.7

AC WAVEFORMS



(1) HC : V_M = 50%; V_I = GND to V_{CC}.
HCT: V_M = 1.3 V; V_I = GND to 3 V.

Fig.7 Waveforms showing the input (nA) to output (nY) propagation delays and the output transition times.

PACKAGE OUTLINES

See *"74HC/HCT/HCU/HCMOS Logic Package Outlines"*.